

# What is a Power MOSFET/IGBT?

## Calculation of Average Loss and Junction Temperature, $T_J$

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## 1. Description

This document describes the calculation of the power MOSFET/IGBT average loss and junction temperature,  $T_J$ .

## 2. Calculation of Average Loss

This section describes the calculation of the average loss when the actual waveform is converted to an approximate waveform. Calculate the total average loss by summing the average losses for each block.

Figure 2-1 shows an example of an approximate waveform.

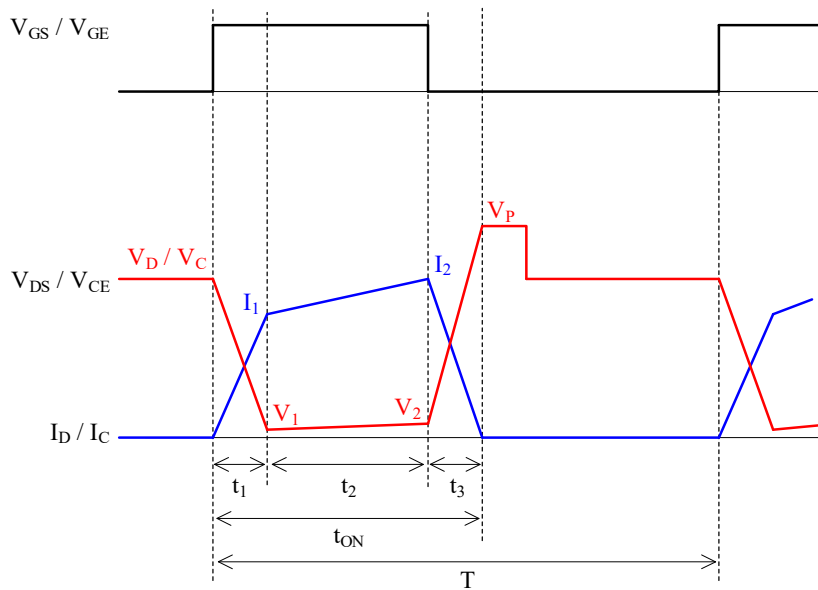


Figure 2-1. Approximate Waveform Example

Where:

- $t_1$  is switching loss time at turn-on,
- $t_2$  is switching loss time at saturation,
- $t_3$  is switching loss time at turn-off,
- $t_{ON}$  is on-time, and
- $T$  is period.

The average loss,  $P_1$ , for the  $t_1$  period is calculated by the following equation.

$$P_1 = \frac{t_1}{6T} (V_D I_1 + 2V_1 I_1)$$

The average loss,  $P_2$ , for the  $t_2$  period is calculated by the following equation.

$$P_2 = \frac{t_2}{6T} (2V_1 I_1 + V_1 I_2 + 2V_2 I_2 + V_2 I_1)$$

The average loss,  $P_3$ , for the  $t_3$  period is calculated by the following equation.

$$P_3 = \frac{t_3}{6T} (V_P I_2 + 2V_2 I_2)$$

Thus, the total average loss,  $P_{ON}$ , is calculated by the following equation.

$$P_{ON} = P_1 + P_2 + P_3$$

### 3. Calculation of Junction Temperature, $T_J$

#### 3.1. Calculation from Case Temperature

Junction temperature,  $T_J$  is estimated from the measured values of loss and case temperature,  $T_C$  during the power MOSFET/IGBT operation and the thermal resistance,  $R_{\theta JC}$  described in the electrical characteristics of the data sheet.

Figure 3-1 shows a conceptual diagram of thermal resistance,  $R_{\theta JC}$ . The specified position of temperature depends on the package and product.

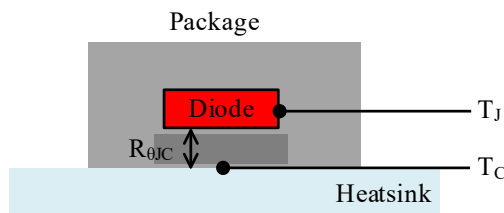


Figure 3-1. Conceptual Diagram of Thermal Resistance,  $R_{\theta JC}$  (Case Temperature)

The symbols in Figure 3-1 represent as follows:

- $T_J$  is junction temperature,
- $T_C$  is case temperature, and
- $R_{\theta JC}$  is thermal resistance between junction and case.

$T_J$  is calculated by the following equations.

$$T_J = P \times R_{\theta JC} + T_C$$

Where:

$P$  is the loss of the power MOSFET/IGBT (W),  
 $R_{\theta JC}$  is thermal resistance between junction and case ( $^{\circ}\text{C}/\text{W}$ ), and  
 $T_C$  is case temperature ( $^{\circ}\text{C}$ ).

As an example, when  $P = 0.6 \text{ W}$ ,  $R_{\theta JC} = 20 \text{ }^{\circ}\text{C}/\text{W}$ , and  $T_C = 80 \text{ }^{\circ}\text{C}$ ,  $T_J$  is calculated by the following equation.

$$T_J = 0.6 \times 20 + 80 = 92 \text{ } (^{\circ}\text{C})$$

### 3.2. Calculation from Transient Thermal Resistance Characteristics

$T_J$  when power is applied instantaneously is estimated from the transient thermal resistance data.  $T_J$  is calculated by the following equation.

$$T_J = P \times r_{\theta JC} + T_C$$

Where:

$P$  is the loss of the power MOSFET/IGBT (W),  
 $r_{\theta JC}$  is transient thermal resistance between junction and case temperature ( $^{\circ}\text{C}/\text{W}$ ), and  
 $T_C$  is case temperature ( $^{\circ}\text{C}$ ).

Figure 3-2 shows the transient thermal resistance characteristics example. For example, when a single square pulse of 100 ms is applied,  $r_{\theta JC}$  is  $2 \text{ }^{\circ}\text{C}/\text{W}$ .

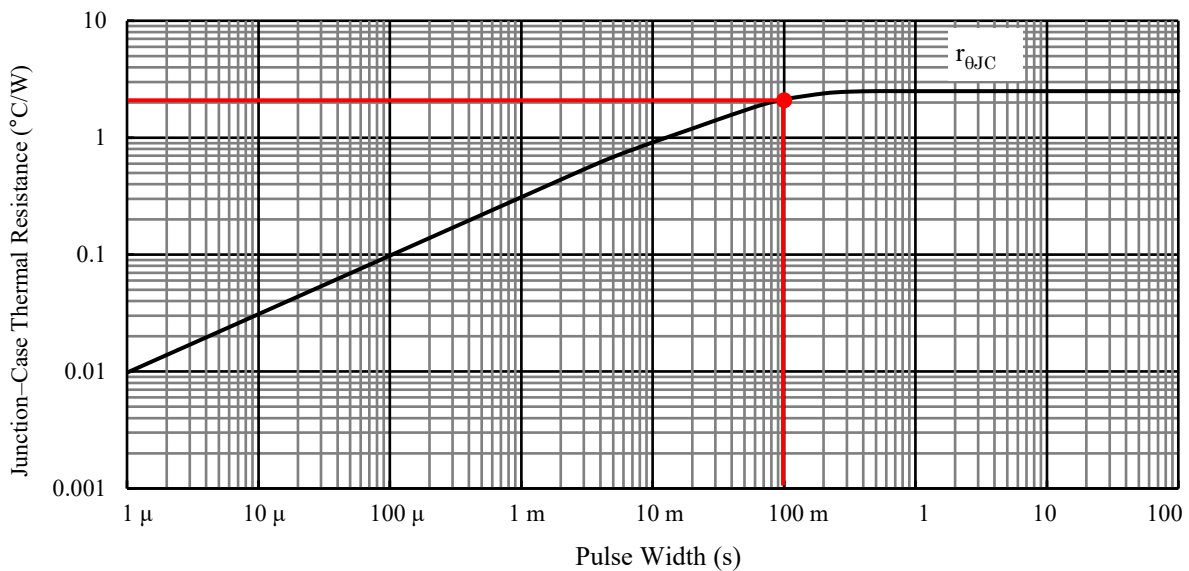


Figure 3-2. Transient Thermal Resistance Characteristics Example

For example, when  $P = 0.6 \text{ W}$ ,  $r_{\theta JC} = 2 \text{ }^{\circ}\text{C}/\text{W}$ , and  $T_C = 100 \text{ }^{\circ}\text{C}$ ,  $T_J$  is calculated by the following equation.

$$T_J = 0.6 \times 2 + 100 = 101.2 \text{ } (^{\circ}\text{C})$$

### **3.3. Calculation Using Superposition Theorem**

This section shows the calculation of the junction temperature,  $T_J$ , when a regular square wave power loss occurs in the power MOSFET/IGBT and the junction temperature,  $T_J$ , when an irregular square wave power loss occurs in the power MOSFET/IGBT. For such power loss waveforms, it is easy and effective to read the thermal resistance in each period from the transient thermal resistance characteristic graph in the data sheet and use the superposition theorem.

### 3.3.1. Continuous Pulse

(A) in Figure 3-3 shows the calculation of the junction temperature,  $T_J$ , when a regular square wave power loss occurs in the power MOSFET/IGBT. To easily calculate  $T_J$ , assume that power losses for two cycles occur in the average power loss over the entire period.

As shown in (B) and (C) in Figure 3-3,  $T_J$  is calculated by approximating the power loss and using the superposition theorem.

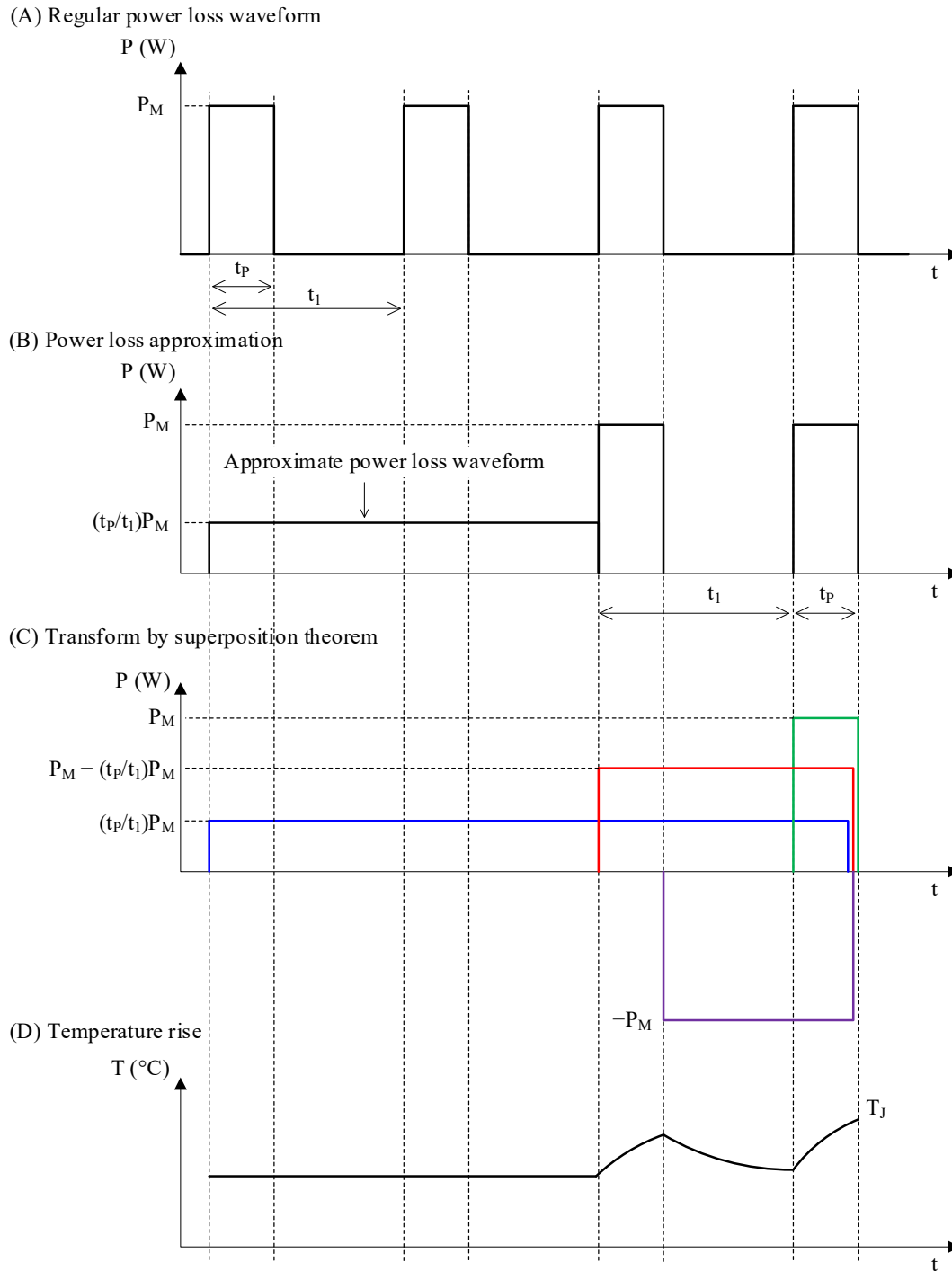


Figure 3-3. Superposition Theorem

Next, the junction temperature is calculated for each block in (C) in Figure 3-3.

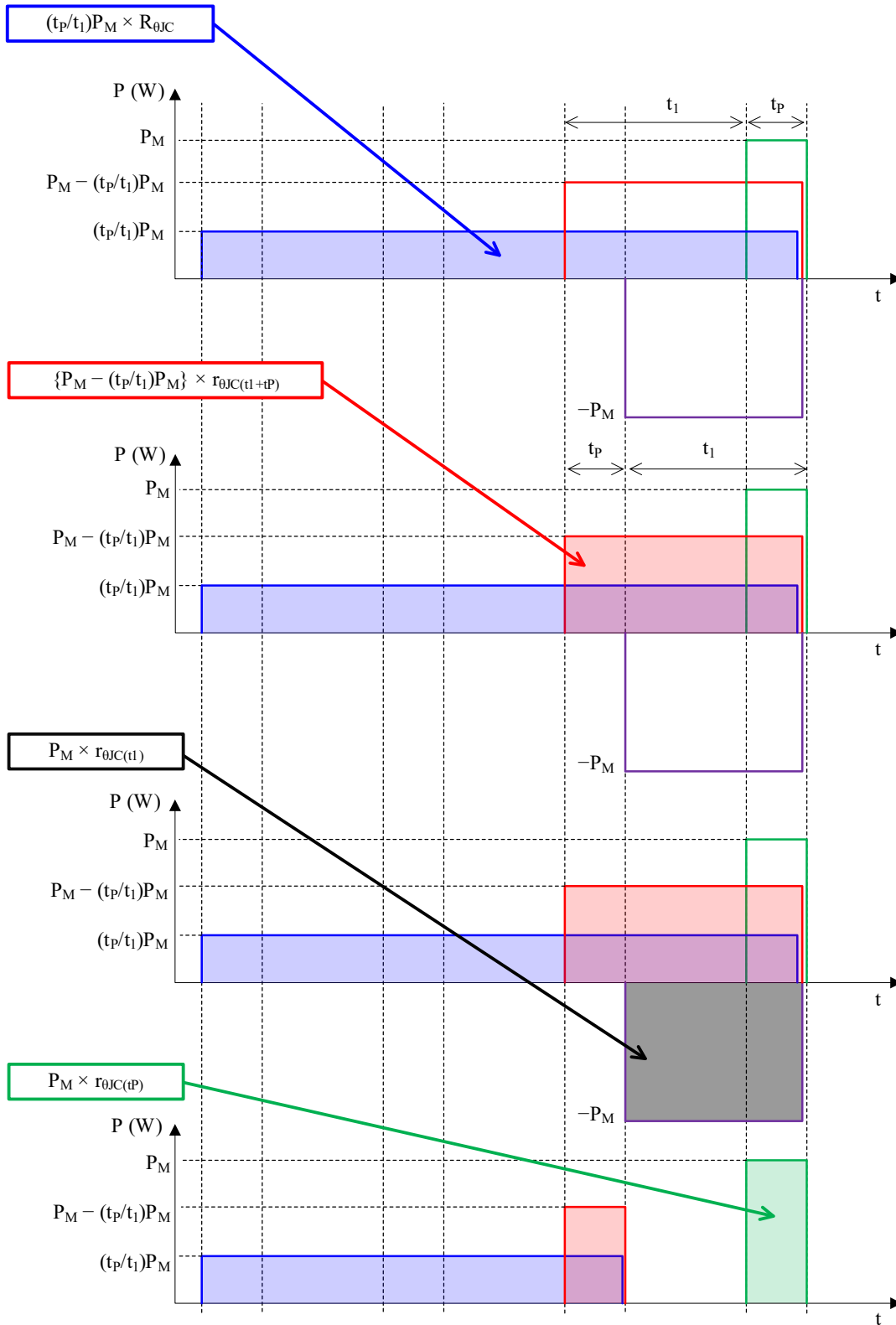


Figure 3-4.  $T_j$  of Each Block



Thus,  $T_J$  when using the superposition theorem is calculated by the following equation.

$$T_J = T_C + P_M \times \left\{ \left( \frac{t_p}{t_1} \right) \times R_{\theta JC} + \left( 1 - \frac{t_p}{t_1} \right) \times r_{\theta JC(t_1+t_p)} - r_{\theta JC(t_1)} + r_{\theta JC(t_p)} \right\}$$

Where:

$T_C$  is case temperature ( $^{\circ}\text{C}$ ),

$P_M$  is average power loss (W),

$t_1$  is period (s),

$t_p$  is pulse width (s),

$R_{\theta JC}$  is the steady-state thermal resistance between junction and case temperature ( $^{\circ}\text{C}/\text{W}$ ),

$r_{\theta JC(t_1+t_p)}$  is the thermal resistance between junction and case temperature in the period,  $t_1+t_p$  ( $^{\circ}\text{C}/\text{W}$ ),

$r_{\theta JC(t_1)}$  is the thermal resistance between junction and case temperature in the period,  $t_1$  ( $^{\circ}\text{C}/\text{W}$ ), and

$r_{\theta JC(t_p)}$  is the thermal resistance between junction and case temperature in the period,  $t_p$  ( $^{\circ}\text{C}/\text{W}$ ).

### 3.3.2. Irregular Pulse

(A) in Figure 3-5 shows the calculation of the junction temperature,  $T_J$ , when an irregular square wave power loss occurs in the power MOSFET/IGBT. As shown in (B) in Figure 3-5,  $T_J$  for each block is calculated by using the superposition theorem.

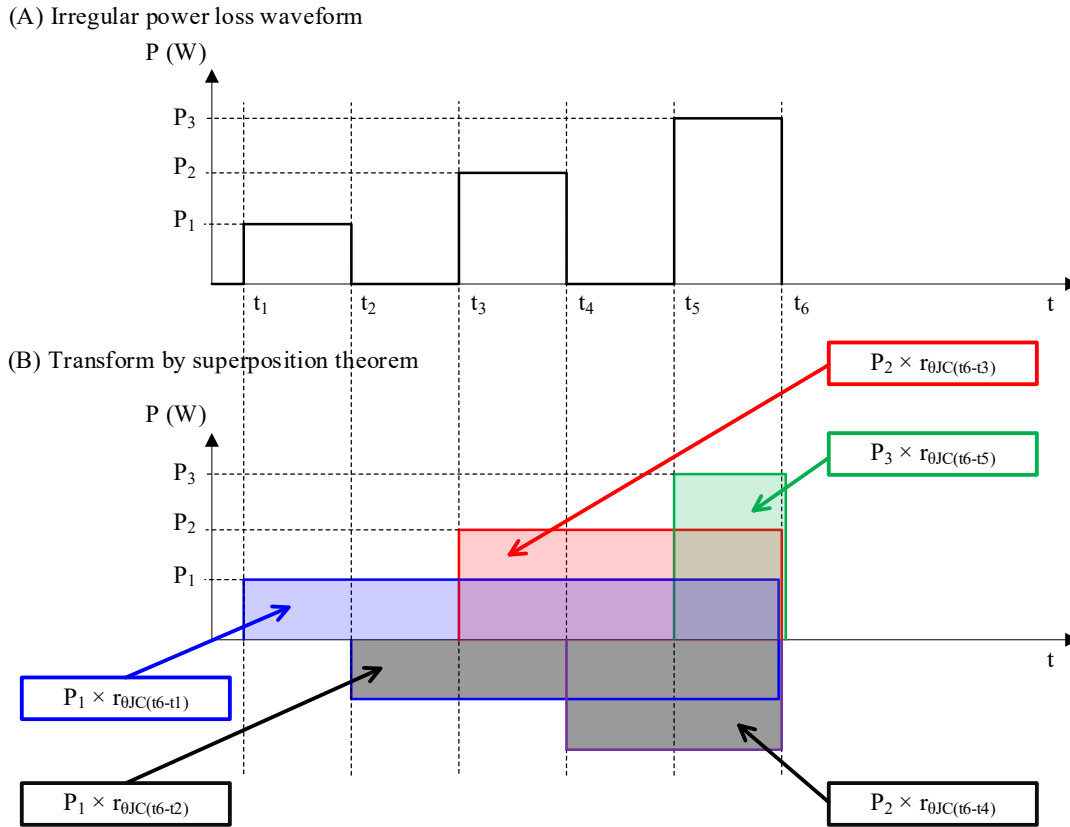


Figure 3-5. Superposition Theorem

Thus,  $T_J$  when using the superposition theorem is calculated by the following equation.

$$T_J = T_C + P_1\{r_{\theta JC(t6-t1)} - r_{\theta JC(t6-t2)}\} + P_2\{r_{\theta JC(t6-t3)} - r_{\theta JC(t6-t4)}\} + P_3\{r_{\theta JC(t6-t5)}\}$$

Where:

$T_C$  is case temperature ( $^{\circ}C$ ),

$P_1$  to  $P_3$  is power loss for each pulse (W),

$r_{\theta JC(t6-t1)}$  is the thermal resistance between junction and case temperature in the period,  $t_6-t_1$  ( $^{\circ}C/W$ ),

$r_{\theta JC(t6-t2)}$  is the thermal resistance between junction and case temperature in the period,  $t_6-t_2$  ( $^{\circ}C/W$ ),

$r_{\theta JC(t6-t3)}$  is the thermal resistance between junction and case temperature in the period,  $t_6-t_3$  ( $^{\circ}C/W$ ),

$r_{\theta JC(t6-t4)}$  is the thermal resistance between junction and case temperature in the period,  $t_6-t_4$  ( $^{\circ}C/W$ ), and

$r_{\theta JC(t6-t5)}$  is the thermal resistance between junction and case temperature in the period,  $t_6-t_5$  ( $^{\circ}C/W$ ).

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